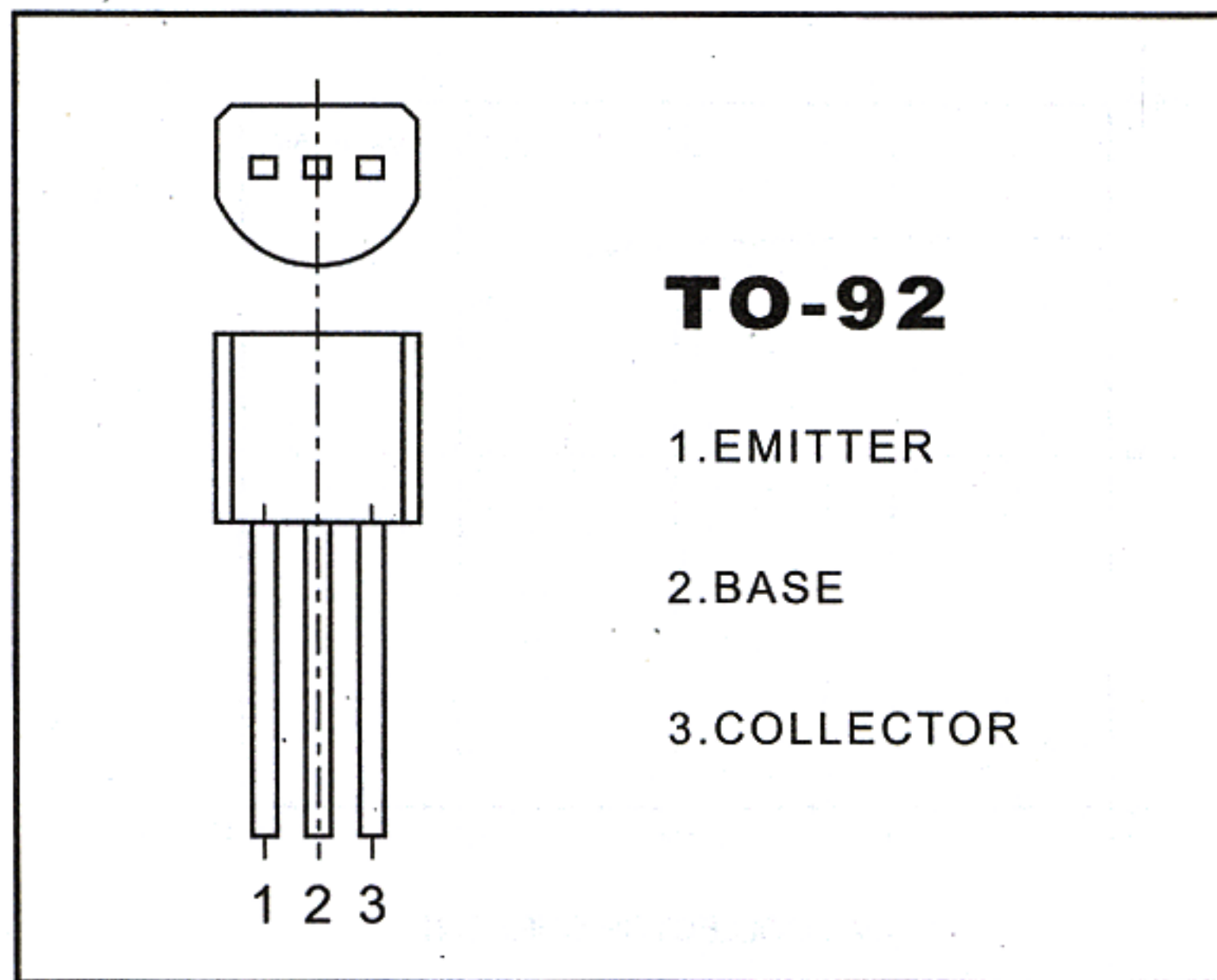


S9015 TRANSISTOR(PNP)



FEATURES

Power dissipation

P_{CM} : 0.45W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.1 A

Collector-base voltage

$V_{(BR)CBO}$: -50 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A, I_E = 0$	-50		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 mA, I_B = 0$	-45		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100 \mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -50 V, I_E = 0$		-0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 V, I_C = 0$		-0.05	μA
DC current gain	h_{FE}	$V_{CE} = -5 V, I_C = -1 mA$	60	1000	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -100 mA, I_B = -10 mA$		-0.3	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = -100 mA, I_B = -10 mA$		-1	V
Transition frequency	f_T	$V_{CE} = -5 V, I_C = -10 mA$ $f = 30 MHz$	150		MHz

CLASSIFICATION OF h_{FE}

Rank	A	B	C	D
Range	60-150	100-300	200-600	400-1000

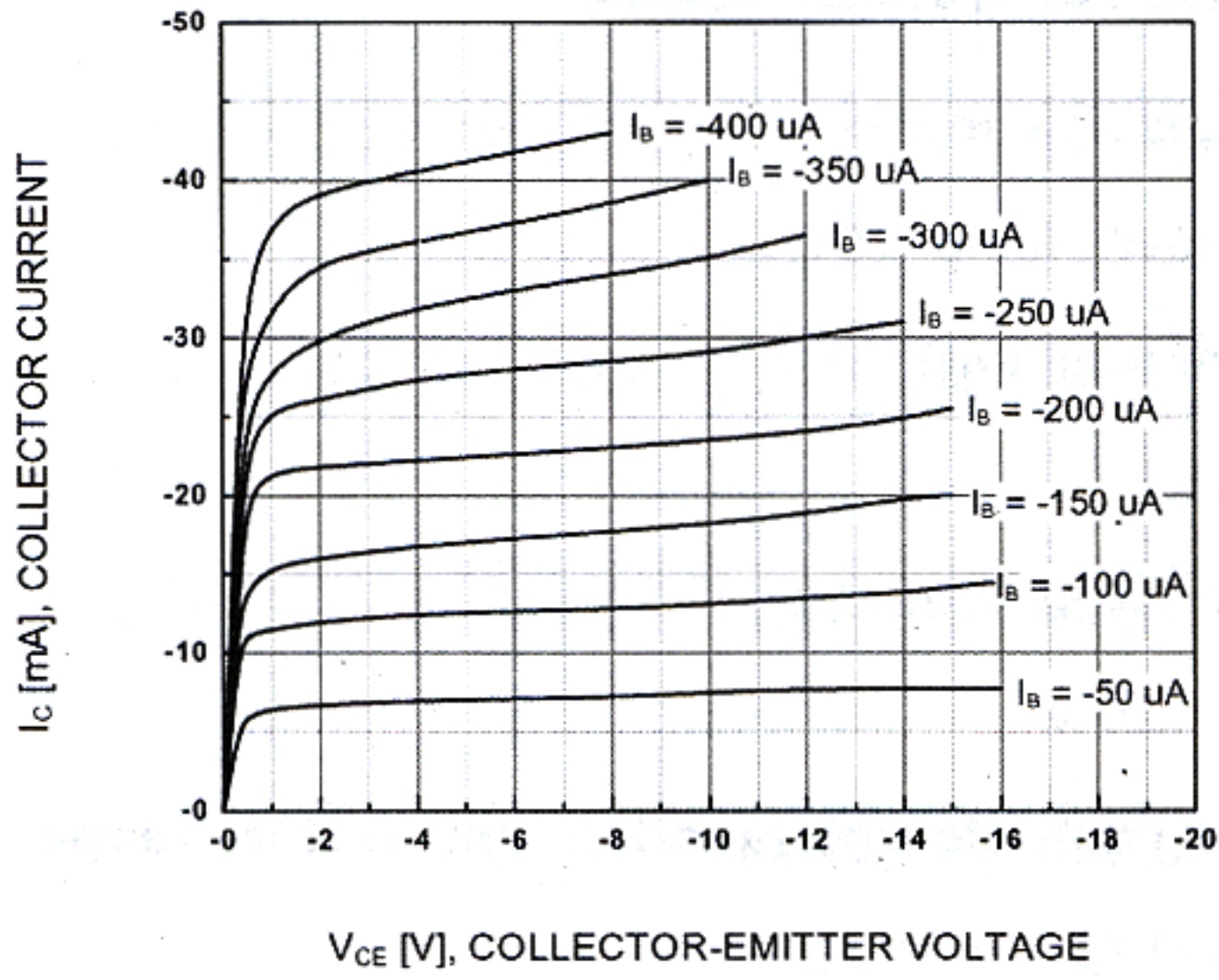


Figure 1. Static Characteristic

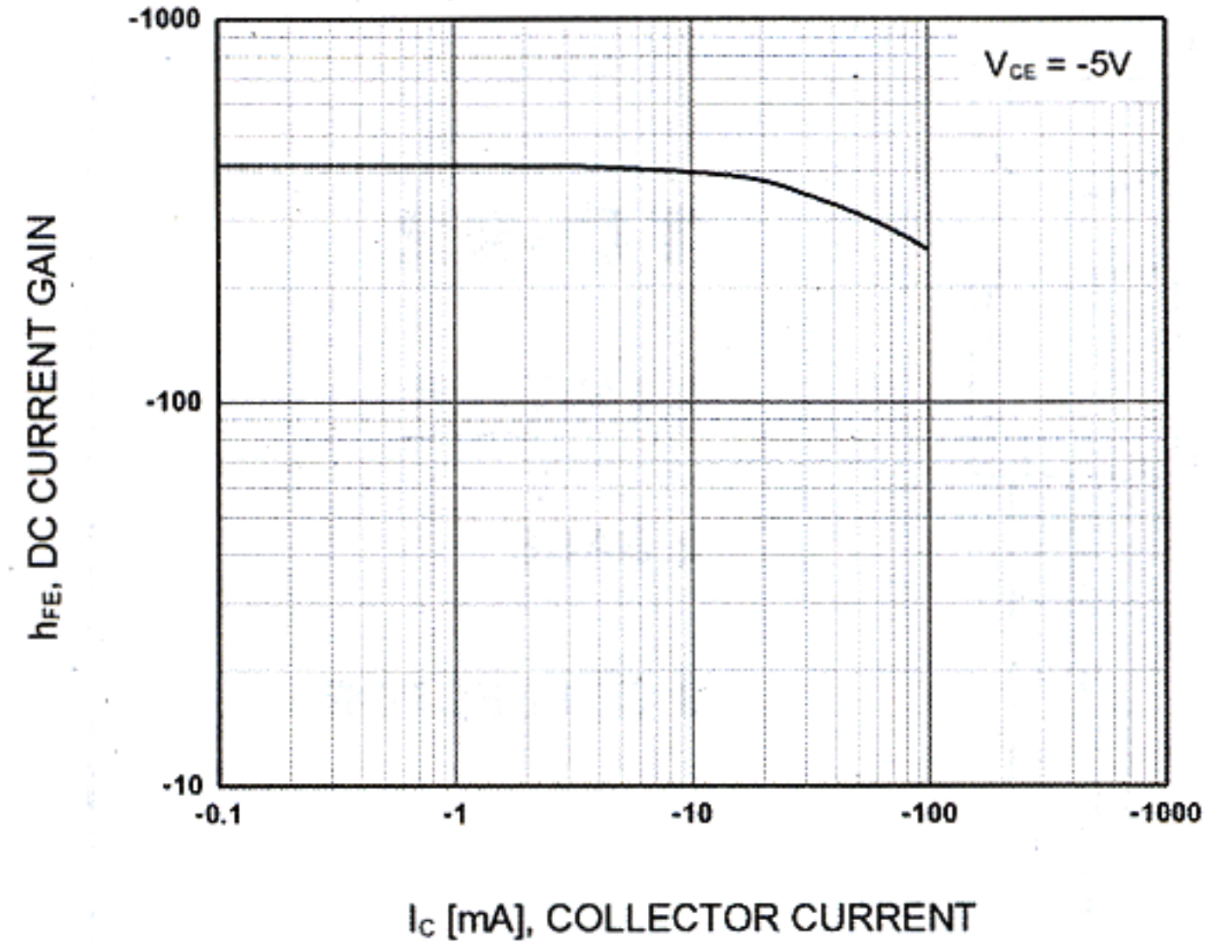


Figure 2. DC current Gain

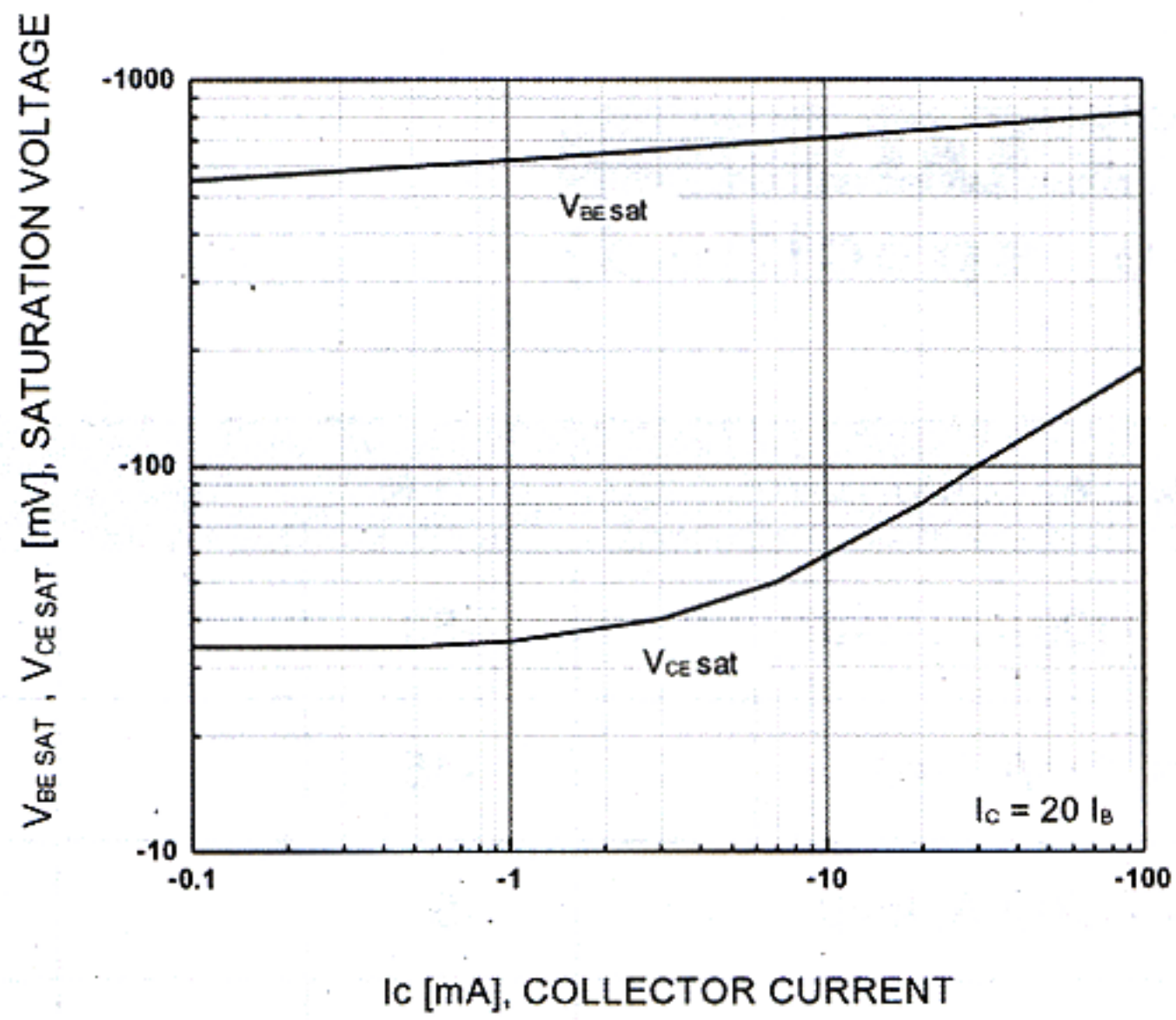


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

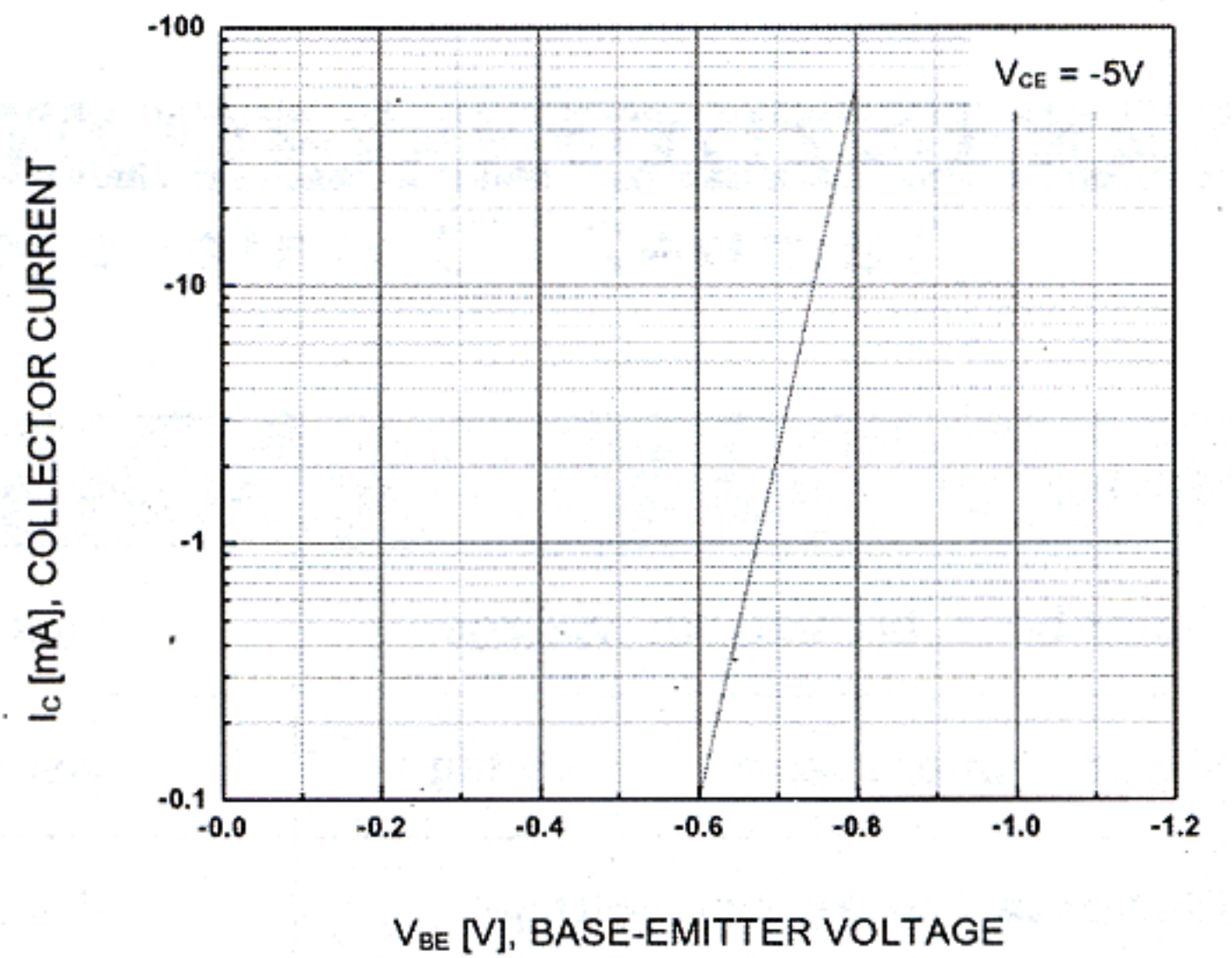


Figure 4. Base-Emitter On Voltage

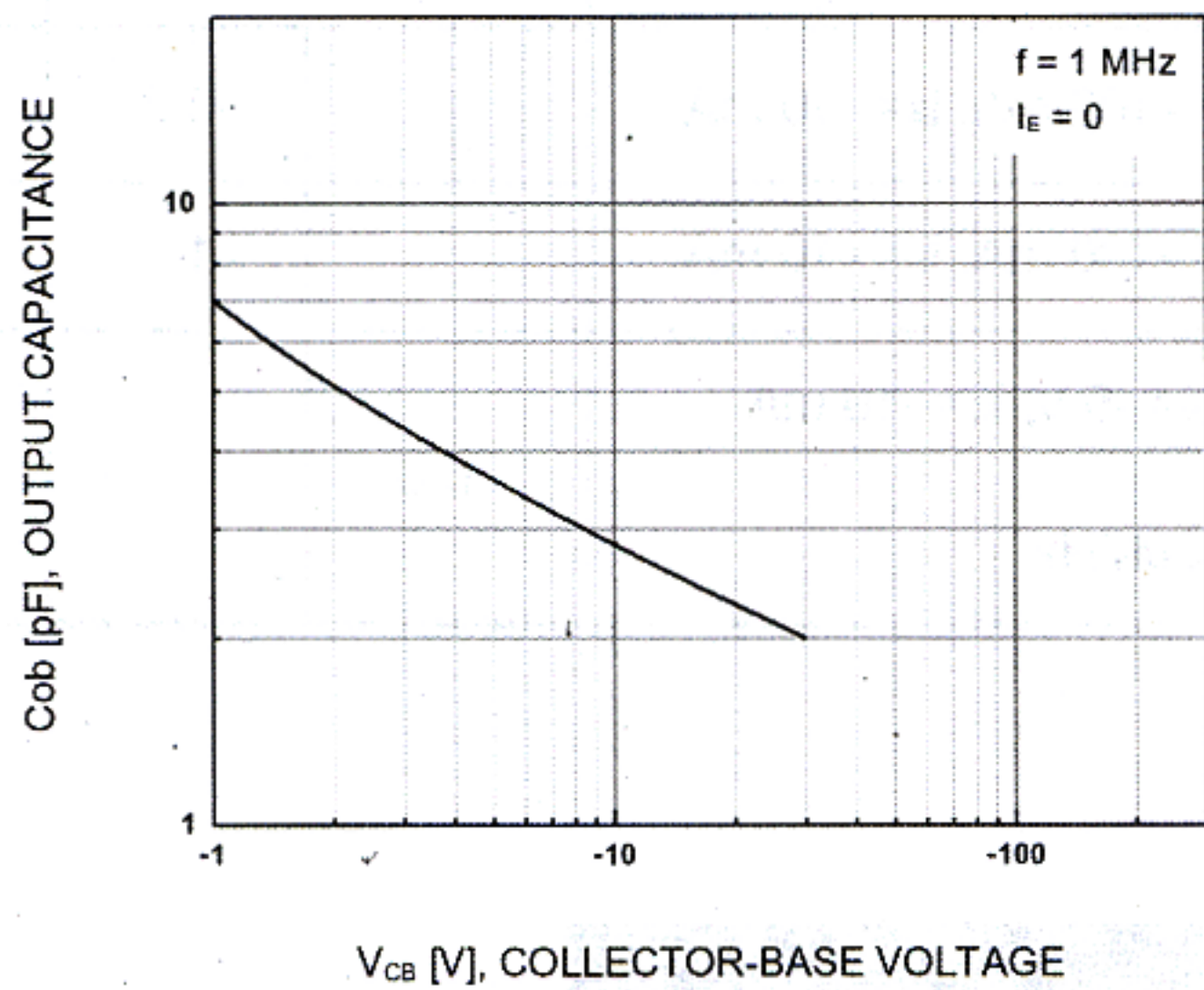


Figure 5. Collector Output Capacitance

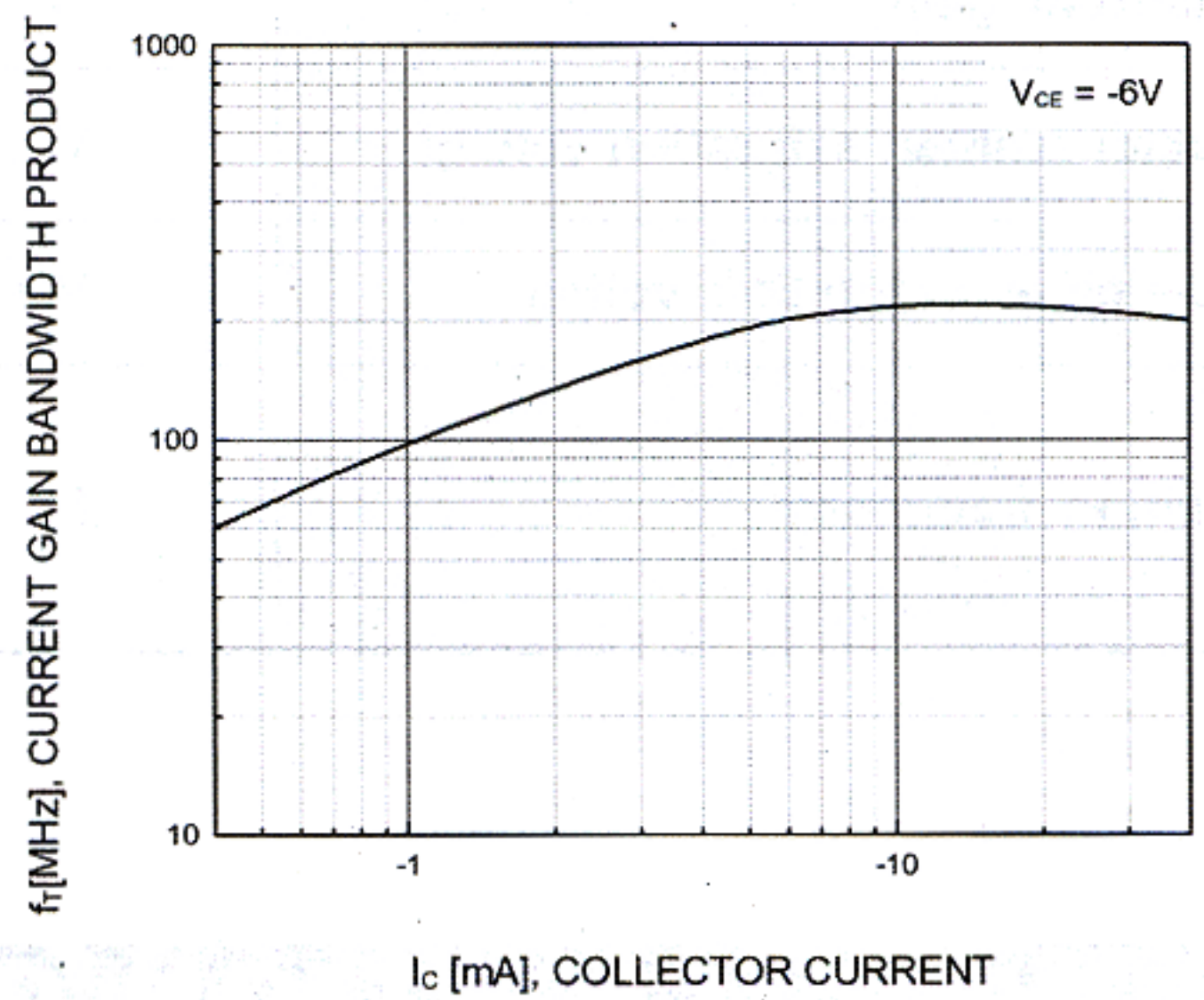


Figure 6. Current Gain Bandwidth Product